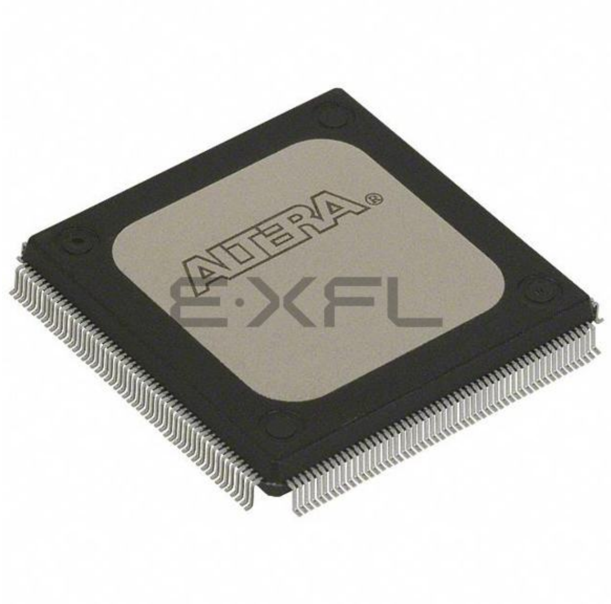

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

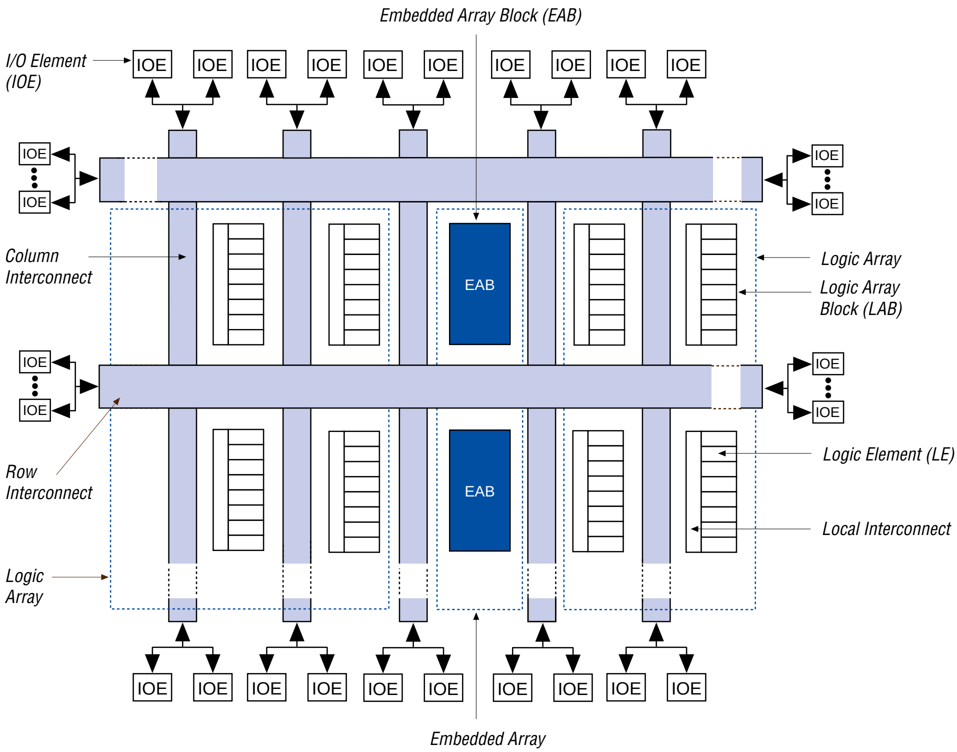
Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	216
Number of Logic Elements/Cells	1728
Total RAM Bits	12288
Number of I/O	147
Number of Gates	69000
Voltage - Supply	4.75V ~ 5.25V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	208-BFQFP Exposed Pad
Supplier Device Package	208-RQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k30rc208-4

- Flexible interconnect
  - FastTrack® Interconnect continuous routing structure for fast, predictable interconnect delays
  - Dedicated carry chain that implements arithmetic functions such as fast adders, counters, and comparators (automatically used by software tools and megafunctions)
  - Dedicated cascade chain that implements high-speed, high-fan-in logic functions (automatically used by software tools and megafunctions)
  - Tri-state emulation that implements internal tri-state buses
  - Up to six global clock signals and four global clear signals
- Powerful I/O pins
  - Individual tri-state output enable control for each pin
  - Open-drain option on each I/O pin
  - Programmable output slew-rate control to reduce switching noise
  - FLEX 10KA devices support hot-socketing
- Peripheral register for fast setup and clock-to-output delay
- Flexible package options
  - Available in a variety of packages with 84 to 600 pins (see Tables 4 and 5)
  - Pin-compatibility with other FLEX 10K devices in the same package
  - FineLine BGA™ packages maximize board space efficiency
- Software design support and automatic place-and-route provided by Altera development systems for Windows-based PCs and Sun SPARCstation, HP 9000 Series 700/800 workstations
- Additional design entry and simulation support provided by EDIF 2 0 0 and 3 0 0 netlist files, library of parameterized modules (LPM), DesignWare components, Verilog HDL, VHDL, and other interfaces to popular EDA tools from manufacturers such as Cadence, Exemplar Logic, Mentor Graphics, OrCAD, Synopsys, Synplicity, VeriBest, and Viewlogic

Figure 1. FLEX 10K Device Block Diagram



FLEX 10K devices provide six dedicated inputs that drive the flipflops' control inputs to ensure the efficient distribution of high-speed, low-skew (less than 1.5 ns) control signals. These signals use dedicated routing channels that provide shorter delays and lower skews than the FastTrack Interconnect. Four of the dedicated inputs drive four global signals. These four global signals can also be driven by internal logic, providing an ideal solution for a clock divider or an internally generated asynchronous clear signal that clears many registers in the device.

Embedded Array Block

The EAB is a flexible block of RAM with registers on the input and output ports, and is used to implement common gate array megafunctions. The EAB is also suitable for functions such as multipliers, vector scalars, and error correction circuits, because it is large and flexible. These functions can be combined in applications such as digital filters and microcontrollers.

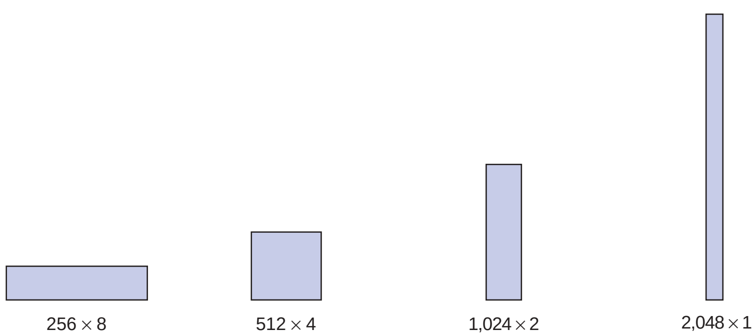
Logic functions are implemented by programming the EAB with a read-only pattern during configuration, creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of EABs. The large capacity of EABs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or field-programmable gate array (FPGA) RAM blocks. For example, a single EAB can implement a 4 × 4 multiplier with eight inputs and eight outputs. Parameterized functions such as LPM functions can automatically take advantage of the EAB.

The EAB provides advantages over FPGAs, which implement on-board RAM as arrays of small, distributed RAM blocks. These FPGA RAM blocks contain delays that are less predictable as the size of the RAM increases. In addition, FPGA RAM blocks are prone to routing problems because small blocks of RAM must be connected together to make larger blocks. In contrast, EABs can be used to implement large, dedicated blocks of RAM that eliminate these timing and routing concerns.

EABs can be used to implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (`WE`) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the `WE` signal. In contrast, the EAB's synchronous RAM generates its own `WE` signal and is self-timed with respect to the global clock. A circuit using the EAB's self-timed RAM need only meet the setup and hold time specifications of the global clock.

When used as RAM, each EAB can be configured in any of the following sizes: 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. See Figure 2.

Figure 2. EAB Memory Configurations



Normal Mode

The normal mode is suitable for general logic applications and wide decoding functions that can take advantage of a cascade chain. In normal mode, four data inputs from the LAB local interconnect and the carry-in are inputs to a four-input LUT. The Compiler automatically selects the carry-in or the DATA3 signal as one of the inputs to the LUT. The LUT output can be combined with the cascade-in signal to form a cascade chain through the cascade-out signal. Either the register or the LUT can be used to drive both the local interconnect and the FastTrack Interconnect at the same time.

The LUT and the register in the LE can be used independently; this feature is known as register packing. To support register packing, the LE has two outputs; one drives the local interconnect and the other drives the FastTrack Interconnect. The DATA4 signal can drive the register directly, allowing the LUT to compute a function that is independent of the registered signal; a three-input function can be computed in the LUT, and a fourth independent signal can be registered. Alternatively, a four-input function can be generated, and one of the inputs to this function can be used to drive the register. The register in a packed LE can still use the clock enable, clear, and preset signals in the LE. In a packed LE, the register can drive the FastTrack Interconnect while the LUT drives the local interconnect, or vice versa.

Arithmetic Mode

The arithmetic mode offers 2 three-input LUTs that are ideal for implementing adders, accumulators, and comparators. One LUT computes a three-input function, and the other generates a carry output. As shown in Figure 9 on page 19, the first LUT uses the carry-in signal and two data inputs from the LAB local interconnect to generate a combinatorial or registered output. For example, in an adder, this output is the sum of three signals: a, b, and carry-in. The second LUT uses the same three signals to generate a carry-out signal, thereby creating a carry chain. The arithmetic mode also supports simultaneous use of the cascade chain.

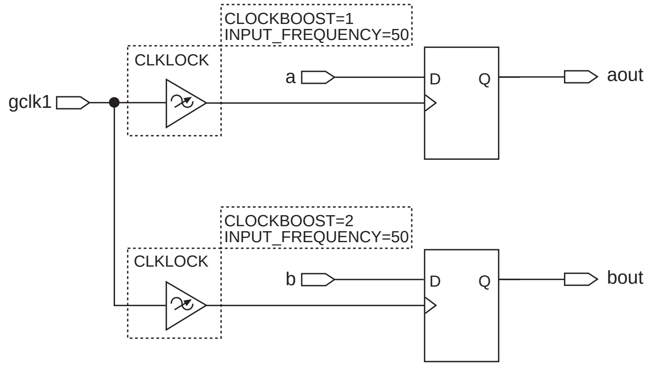
Each IOE selects the clock, clear, clock enable, and output enable controls from a network of I/O control signals called the peripheral control bus. The peripheral control bus uses high-speed drivers to minimize signal skew across devices; it provides up to 12 peripheral control signals that can be allocated as follows:

- Up to eight output enable signals
- Up to six clock enable signals
- Up to two clock signals
- Up to two clear signals

If more than six clock enable or eight output enable signals are required, each IOE on the device can be controlled by clock enable and output enable signals driven by specific LEs. In addition to the two clock signals available on the peripheral control bus, each IOE can use one of two dedicated clock pins. Each peripheral control signal can be driven by any of the dedicated input pins or the first LE of each LAB in a particular row. In addition, an LE in a different row can drive a column interconnect, which causes a row interconnect to drive the peripheral control signal. The chip-wide reset signal will reset all IOE registers, overriding any other control signals.

Tables 8 and 9 list the sources for each peripheral control signal, and the rows that can drive global signals. These tables also show how the output enable, clock enable, clock, and clear signals share 12 peripheral control signals.

Figure 17. Enabling ClockLock & ClockBoost in the Same Design



To use both the ClockLock and ClockBoost circuits in the same design, designers must use Revision C EPF10K100GC503-3DX devices and MAX+PLUS II software versions 7.2 or higher. The die revision is indicated by the third digit of the nine-digit code on the top side of the device.

Output Configuration

This section discusses the peripheral component interconnect (PCI) pull-up clamping diode option, slew-rate control, open-drain output option, MultiVolt I/O interface, and power sequencing for FLEX 10K devices. The PCI pull-up clamping diode, slew-rate control, and open-drain output options are controlled pin-by-pin via Altera logic options. The MultiVolt I/O interface is controlled by connecting V_{CCIO} to a different voltage than V_{CCINT}. Its effect can be simulated in the Altera software via the **Global Project Device Options** dialog box (Assign menu).

PCI Clamping Diodes

The EPF10K10A and EPF10K30A devices have a pull-up clamping diode on every I/O, dedicated input, and dedicated clock pin. PCI clamping diodes clamp the transient overshoot caused by reflected waves to the V_{CCIO} value and are required for 3.3-V PCI compliance. Clamping diodes can also be used to limit overshoot in other systems.

Clamping diodes are controlled on a pin-by-pin basis via a logic option in the Altera software. When V_{CCIO} is 3.3 V, a pin that has the clamping diode turned on can be driven by a 2.5-V or 3.3-V signal, but not a 5.0-V signal. When V_{CCIO} is 2.5 V, a pin that has the clamping diode turned on can be driven by a 2.5-V signal, but not a 3.3-V or 5.0-V signal. However, a clamping diode can be turned on for a subset of pins, which allows devices to bridge between a 3.3-V PCI bus and a 5.0-V device.

Table 24. EPF10K50V & EPF10K130V Device DC Operating Conditions *Notes (6), (7)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level input voltage		2.0		5.75	V
V_{IL}	Low-level input voltage		–0.5		0.8	V
V_{OH}	3.3-V high-level TTL output voltage	I_{OH} = –8 mA DC *(8)*	2.4			V
	3.3-V high-level CMOS output voltage	I_{OH} = –0.1 mA DC *(8)*	V_{CCIO} – 0.2			V
V_{OL}	3.3-V low-level TTL output voltage	I_{OL} = 8 mA DC *(9)*			0.45	V
	3.3-V low-level CMOS output voltage	I_{OL} = 0.1 mA DC *(9)*			0.2	V
I_I	Input pin leakage current	V_I = 5.3 V to –0.3 V *(10)*	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = 5.3 V to –0.3 V *(10)*	–10		10	µA
I_{CC0}	V_{CC} supply current (standby)	V_I = ground, no load		0.3	10	mA
		V_I = ground, no load *(11)*		10		mA

Table 25. EPF10K50V & EPF10K130V Device Capacitance *(12)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		10	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		15	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		10	pF

Notes to tables:

(1) See the *Operating Requirements for Altera Devices Data Sheet*.
(2) Minimum DC input voltage is –0.5 V. During transitions, the inputs may undershoot to –2.0 V or overshoot to 5.75 V for input currents less than 100 mA and periods shorter than 20 ns.
(3) Numbers in parentheses are for industrial-temperature-range devices.
(4) Maximum V_{CC} rise time is 100 ms. V_{CC} must rise monotonically.
(5) EPF10K50V and EPF10K130V device inputs may be driven before V_{CCINT} and V_{CCIO} are powered.
(6) Typical values are for T_A = 25° C and V_{CC} = 3.3 V.
(7) These values are specified under the EPF10K50V and EPF10K130V device Recommended Operating Conditions in Table 23 on page 48.
(8) The I_{OH} parameter refers to high-level TTL or CMOS output current.
(9) The I_{OL} parameter refers to low-level TTL or CMOS output current. This parameter applies to open-drain pins as well as output pins.
(10) This value is specified for normal device operation. The value may vary during power-up.
(11) This parameter applies to -1 speed grade EPF10K50V devices, -2 speed grade EPF10K50V industrial temperature devices, and -2 speed grade EPF10K130V devices.
(12) Capacitance is sample-tested only.

Table 36. Interconnect Timing Microparameters *Note (1)*

Symbol	Parameter	Conditions
$t_{DIN2IOE}$	Delay from dedicated input pin to IOE control input	*(7)*
$t_{DCLK2LE}$	Delay from dedicated clock pin to LE or EAB clock	*(7)*
$t_{DIN2DATA}$	Delay from dedicated input or clock to LE or EAB data	*(7)*
$t_{DCLK2IOE}$	Delay from dedicated clock pin to IOE clock	*(7)*
t_{DIN2LE}	Delay from dedicated input pin to LE or EAB control input	*(7)*
$t_{SAMELAB}$	Routing delay for an LE driving another LE in the same LAB	
$t_{SAMEROW}$	Routing delay for a row IOE, LE, or EAB driving a row IOE, LE, or EAB in the same row	*(7)*
$t_{SAMECOLUMN}$	Routing delay for an LE driving an IOE in the same column	*(7)*
$t_{DIFFROW}$	Routing delay for a column IOE, LE, or EAB driving an LE or EAB in a different row	*(7)*
$t_{TWOROWS}$	Routing delay for a row IOE or EAB driving an LE or EAB in a different row	*(7)*
$t_{LEPERIPH}$	Routing delay for an LE driving a control signal of an IOE via the peripheral control bus	*(7)*
$t_{LABCARRY}$	Routing delay for the carry-out signal of an LE driving the carry-in signal of a different LE in a different LAB	
$t_{LABCASC}$	Routing delay for the cascade-out signal of an LE driving the cascade-in signal of a different LE in a different LAB	

Table 37. External Timing Parameters *Notes (8), (10)*

Symbol	Parameter	Conditions
t_{DRR}	Register-to-register delay via four LEs, three row interconnects, and four local interconnects	*(9)*
t_{INSU}	Setup time with global clock at IOE register	
t_{INH}	Hold time with global clock at IOE register	
t_{OUTCO}	Clock-to-output delay with global clock at IOE register	

Table 38. External Bidirectional Timing Parameters *Note (10)*

Symbol	Parameter	Condition
$t_{INSUBIDIR}$	Setup time for bidirectional pins with global clock at adjacent LE register	
$t_{INHBIDIR}$	Hold time for bidirectional pins with global clock at adjacent LE register	
$t_{OUTCOBIDIR}$	Clock-to-output delay for bidirectional pins with global clock at IOE register	
$t_{XZBIDIR}$	Synchronous IOE output buffer disable delay	
$t_{ZXBIDIR}$	Synchronous IOE output buffer enable delay, slow slew rate = off	

Table 49. EPF10K30, EPF10K40 & EPF10K50 Device IOE Timing Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{IOD}		0.4		0.6	ns
t_{IOC}		0.5		0.9	ns
t_{IOCO}		0.4		0.5	ns
t_{IOCOMB}		0.0		0.0	ns
t_{IOSU}	3.1		3.5		ns
t_{IOH}	1.0		1.9		ns
t_{IOCLR}		1.0		1.2	ns
t_{OD1}		3.3		3.6	ns
t_{OD2}		5.6		6.5	ns
t_{OD3}		7.0		8.3	ns
t_{XZ}		5.2		5.5	ns
t_{ZX1}		5.2		5.5	ns
t_{ZX2}		7.5		8.4	ns
t_{ZX3}		8.9		10.2	ns
t_{INREG}		7.7		10.0	ns
t_{IOFD}		3.3		4.0	ns
t_{INCOMB}		3.3		4.0	ns

Table 51. EPF10K30, EPF10K40 & EPF10K50 Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{EABAA}		13.7		17.0	ns
$t_{EABRCCOMB}$	13.7		17.0		ns
$t_{EABRCREG}$	9.7		11.9		ns
t_{EABWP}	5.8		7.2		ns
$t_{EABWCCOMB}$	7.3		9.0		ns
$t_{EABWCREG}$	13.0		16.0		ns
t_{EABDD}		10.0		12.5	ns
$t_{EABDATACO}$		2.0		3.4	ns
$t_{EABDATASU}$	5.3		5.6		ns
$t_{EABDATAH}$	0.0		0.0		ns
$t_{EABWESU}$	5.5		5.8		ns
t_{EABWEH}	0.0		0.0		ns
$t_{EABWDSU}$	5.5		5.8		ns
t_{EABWDH}	0.0		0.0		ns
$t_{EABWASU}$	2.1		2.7		ns
t_{EABWAH}	0.0		0.0		ns
t_{EABWO}		9.5		11.8	ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 57 through 63 show EPF10K70 device internal and external timing parameters.

Table 57. EPF10K70 Device LE Timing Microparameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		1.3		1.5		2.0	ns
t_{CLUT}		0.4		0.4		0.5	ns
t_{RLUT}		1.5		1.6		2.0	ns
t_{PACKED}		0.8		0.9		1.3	ns
t_{EN}		0.8		0.9		1.2	ns
t_{CICO}		0.2		0.2		0.3	ns
t_{CGEN}		1.0		1.1		1.4	ns
t_{CGENR}		1.1		1.2		1.5	ns
t_{CASC}		1.0		1.1		1.3	ns
t_C		0.7		0.8		1.0	ns
t_{CO}		0.9		1.0		1.4	ns
t_{COMB}		0.4		0.5		0.7	ns
t_{SU}	1.9		2.1		2.6		ns
t_H	2.1		2.3		3.1		ns
t_{PRE}		0.9		1.0		1.4	ns
t_{CLR}		0.9		1.0		1.4	ns
t_{CH}	4.0		4.0		4.0		ns
t_{CL}	4.0		4.0		4.0		ns

Table 59. EPF10K70 Device EAB Internal Microparameters *Note (1)*							
Symbol	**-2 Speed Grade**		**-3 Speed Grade**		**-4 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
$t_{EABDATA1}$		1.3		1.5		1.9	ns
$t_{EABDATA2}$		4.3		4.8		6.0	ns
t_{EABWE1}		0.9		1.0		1.2	ns
t_{EABWE2}		4.5		5.0		6.2	ns
t_{EABCLK}		0.9		1.0		2.2	ns
t_{EABCO}		0.4		0.5		0.6	ns
$t_{EABBYPASS}$		1.3		1.5		1.9	ns
t_{EABSU}	1.3		1.5		1.8		ns
t_{EABH}	1.8		2.0		2.5		ns
t_{AA}		7.8		8.7		10.7	ns
t_{WP}	5.2		5.8		7.2		ns
t_{WDSU}	1.4		1.6		2.0		ns
t_{WDH}	0.3		0.3		0.4		ns
t_{WASU}	0.4		0.5		0.6		ns
t_{WAH}	0.9		1.0		1.2		ns
t_{WO}		4.5		5.0		6.2	ns
t_{DD}		4.5		5.0		6.2	ns
t_{EABOUT}		0.4		0.5		0.6	ns
t_{EABCH}	4.0		4.0		4.0		ns
t_{EABCL}	5.2		5.8		7.2		ns

Table 69. EPF10K100 Device External Timing Parameters Note (1)

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		19.1		19.1		24.2	ns
t_{INSU} *(2)*, *(3)*, *(4)*	7.8		7.8		8.5		ns
t_{OUTCO} *(3)*, *(4)*	2.0	11.1	2.0	11.1	2.0	14.3	ns
t_{INH} *(3)*	0.0		0.0		0.0		ns
t_{INSU} *(2)*, *(3)*, *(5)*	6.2		–		–		ns
t_{OUTCO} *(3)*, *(5)*	2.0	6.7		–		–	ns

Table 70. EPF10K100 Device External Bidirectional Timing Parameters Note (1)

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$ *(4)*	8.1		8.1		10.4		ns
$t_{INHBIDIR}$ *(4)*	0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$ *(4)*	2.0	11.1	2.0	11.1	2.0	14.3	ns
$t_{XZBIDIR}$ *(4)*		15.3		15.3		18.4	ns
$t_{ZXBIDIR}$ *(4)*		15.3		15.3		18.4	ns
$t_{INSUBIDIR}$ *(5)*	9.1		–		–		ns
$t_{INHBIDIR}$ *(5)*	0.0		–		–		ns
$t_{OUTCOBIDIR}$ *(5)*	2.0	7.2	–	–	–	–	ns
$t_{XZBIDIR}$ *(5)*		14.3		–		–	ns
$t_{ZXBIDIR}$ *(5)*		14.3		–		–	ns

Notes to tables:

(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.
(4) This parameter is measured without the use of the ClockLock or ClockBoost circuits.
(5) This parameter is measured with the use of the ClockLock or ClockBoost circuits.

Table 95. EPF10K30A Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		9.7		11.6		16.2	ns
$t_{EABRCCOMB}$	9.7		11.6		16.2		ns
$t_{EABRCREG}$	5.9		7.1		9.7		ns
t_{EABWP}	3.8		4.5		5.9		ns
$t_{EABWCCOMB}$	4.0		4.7		6.3		ns
$t_{EABWCREG}$	9.8		11.6		16.6		ns
t_{EABDD}		9.2		11.0		16.1	ns
$t_{EABDATACO}$		1.7		2.1		3.4	ns
$t_{EABDATASU}$	2.3		2.7		3.5		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	3.3		3.9		4.9		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	3.2		3.8		5.0		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	3.7		4.4		5.1		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		6.1		7.3		11.3	ns

Table 102. EPF10K100A Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		6.8		7.8		9.2	ns
$t_{EABRCCOMB}$	6.8		7.8		9.2		ns
$t_{EABRCREG}$	5.4		6.2		7.4		ns
t_{EABWP}	3.2		3.7		4.4		ns
$t_{EABWCCOMB}$	3.4		3.9		4.7		ns
$t_{EABWCREG}$	9.4		10.8		12.8		ns
t_{EABDD}		6.1		6.9		8.2	ns
$t_{EABDATACO}$		2.1		2.3		2.9	ns
$t_{EABDATASU}$	3.7		4.3		5.1		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	2.8		3.3		3.8		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	3.4		4.0		4.6		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	1.9		2.3		2.6		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		5.1		5.7		6.9	ns

Table 109. EPF10K250A Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		6.1		6.8		8.2	ns
$t_{EABRCCOMB}$	6.1		6.8		8.2		ns
$t_{EABRCREG}$	4.6		5.1		6.1		ns
t_{EABWP}	5.6		6.4		7.5		ns
$t_{EABWCCOMB}$	5.8		6.6		7.9		ns
$t_{EABWCREG}$	15.8		17.8		21.0		ns
t_{EABDD}		5.7		6.4		7.8	ns
$t_{EABDATACO}$		0.7		0.8		1.0	ns
$t_{EABDATASU}$	4.5		5.1		5.9		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	8.2		9.3		10.9		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	1.7		1.8		2.1		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	0.9		0.9		1.0		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		5.3		6.0		7.4	ns

Figure 32. $I_{CCACTIVE}$ vs. Operating Frequency (Part 2 of 3)

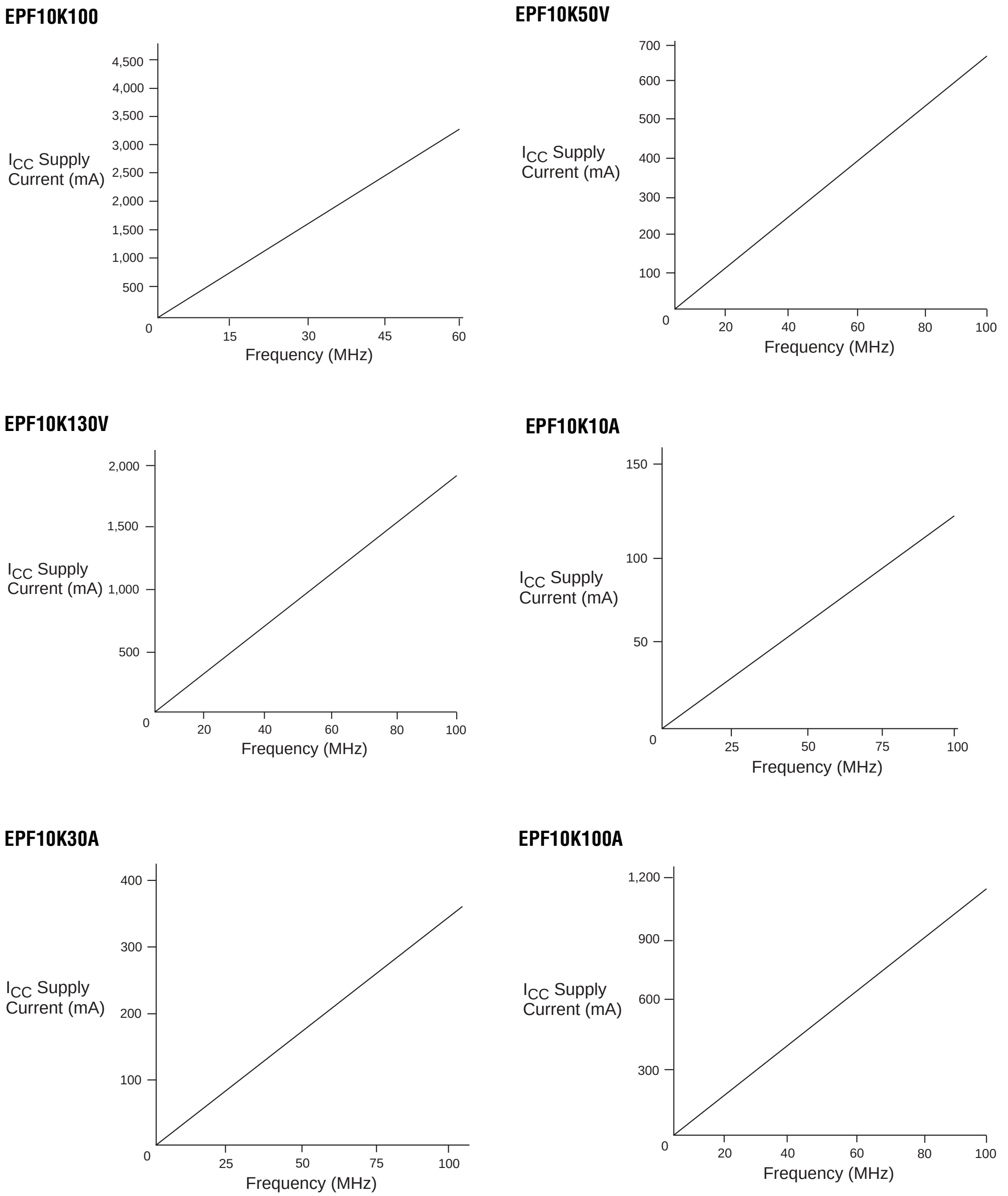
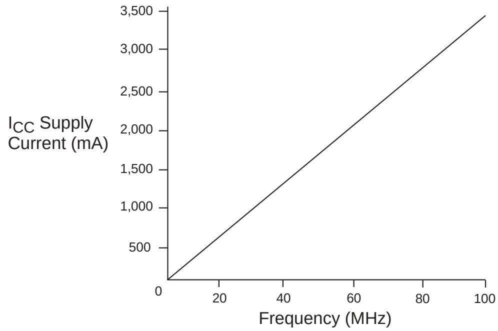


Figure 32. $I_{CCACTIVE}$ vs. Operating Frequency (Part 3 of 3)

EPF10K250A



Configuration & Operation

The FLEX 10K architecture supports several configuration schemes. This section summarizes the device operating modes and available device configuration schemes.

See *Application Note 116 (Configuring APEX 20K, FLEX 10K & FLEX 6000 Devices)* for detailed descriptions of device configuration options, device configuration pins, and for information on configuring FLEX 10K devices, including sample schematics, timing diagrams, and configuration parameters.

Operating Modes

The FLEX 10K architecture uses SRAM configuration elements that require configuration data to be loaded every time the circuit powers up. The process of physically loading the SRAM data into the device is called *configuration*. Before configuration, as VCC rises, the device initiates a Power-On Reset (POR). This POR event clears the device and prepares it for configuration. The FLEX 10K POR time does not exceed 50 µs.

During initialization, which occurs immediately after configuration, the device resets registers, enables I/O pins, and begins to operate as a logic device. The I/O pins are tri-stated during power-up, and before and during configuration. Together, the configuration and initialization processes are called *command mode*; normal device operation is called *user mode*.

Multiple FLEX 10K devices can be configured in any of the five configuration schemes by connecting the configuration enable (nCE) and configuration enable output (nCEO) pins on each device.

Table 116. Data Sources for Configuration

Configuration Scheme	Data Source
Configuration device	EPC1, EPC2, EPC16, or EPC1441 configuration device
Passive serial (PS)	BitBlaster, MasterBlaster, or ByteBlasterMV download cable, or serial data source
Passive parallel asynchronous (PPA)	Parallel data source
Passive parallel synchronous (PPS)	Parallel data source
JTAG	BitBlaster, MasterBlaster, or ByteBlasterMV download cable, or microprocessor with Jam STAPL file or Jam Byte-Code file

Device Pin-Outs

See the Altera web site (**http://www.altera.com**) or the Altera Digital Library for pin-out information.

Revision History

The information contained in the *FLEX 10K Embedded Programmable Logic Device Family Data Sheet* version 4.2 supersedes information published in previous versions.

Version 4.2 Changes

The following change was made to version 4.2 of the *FLEX 10K Embedded Programmable Logic Device Family Data Sheet*: updated Figure 13.

Version 4.1 Changes

The following changes were made to version 4.1 of the *FLEX 10K Embedded Programmable Logic Device Family Data Sheet*.

- Updated General Description section
- Updated I/O Element section
- Updated SameFrame Pin-Outs section
- Updated Figure 16
- Updated Tables 13 and 116
- Added Note 9 to Table 19
- Added Note 10 to Table 24
- Added Note 10 to Table 28

Notes: